

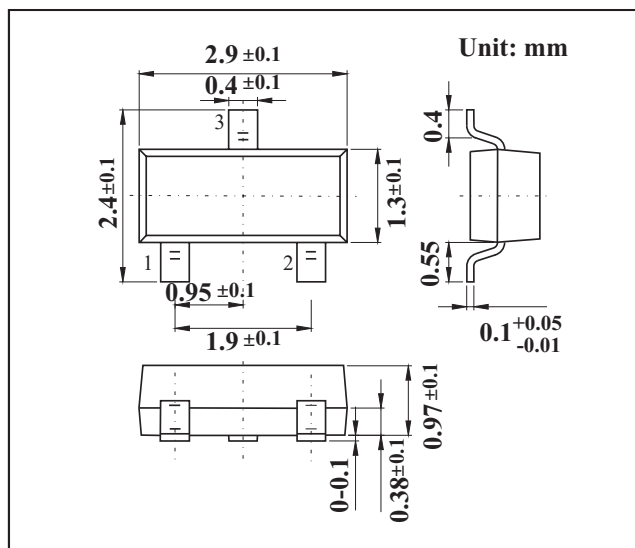
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- High DC Current gain
- Low Output Capacitance
- General Small Signal Amplifier
- Transistor NPN

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Units
Collector - Base Voltage	V _{CBO}	30	V
Collector - Emitter Voltage	V _{CEO}	25	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	700	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	

Parameter	Symbol	Test Conditons	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 100 μA, I _E = 0	30			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	25			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 μ A, I _C = 0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 30 V , I _E = 0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V , I _C =0			100	
Collector-emitter saturation voltage (Note.1)	V _{CE(sat)}	I _C =700 mA, I _B =70mA			0.6	V
Base - emitter saturation voltage (Note.1)	V _{BE(sat)}	I _C =700 mA, I _B =70mA			1.2	
Base - emitter voltage (Note.1)	V _{BE}	V _{CE} = 6V, I _C = 10mA	0.6		0.7	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = 1V, I _C = 100mA	110		400	
	h _{FE(2)}	V _{CE} = 1V, I _C = 700mA	50			
Collector output capacitance	C _{ob}	V _{CB} = 6V, I _E = 10mA , f=10MHz		12		pF
Transition frequency	f _T	V _{CE} = 6V, I _C = 10mA	170			MHz

Note.1: Pulse test : Pulse width ≤350μs,Duty Cycle≤2%

RATINGS AND CHARACTERISTIC CURVES

